

ABSTRACT

SILVER-ALLOY SPUTTERING TARGET FOR CONDUCTIVE-FILM FORMATION,
AND METHOD FOR PRODUCING SAME

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An aspect of this sputtering target has a component composition including 0.1 mass% to 1.5 mass% of In with a remainder of Ag and inevitable impurities, wherein an average grain diameter of crystal grains in an alloy is in a range of 30 μm or more to less than 150 μm , and a dispersion of grain diameters of the crystal grains is 20% or less of the average grain diameter. An aspect of this method for producing a sputtering target includes: subjecting a cast ingot having the above-described component composition to a hot rolling step, a cooling step and a machining step sequentially, wherein in the hot rolling step, one or more passes of finish hot rolling are carried out under conditions where a rolling reduction rate per pass is in a range of 20% to 50%, a strain rate is in a range of 3 /sec to 15 /sec, and a temperature after the pass is in a range of 400°C to 650°C, and in the cooling step, quenching is carried out at a cooling rate in a range of 200 °C/min to 1000 °C/min.

NO FIGURE.